TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

155368

ULTRA HIGH SPEED SWITCHING APPLICATION

• Small Package

• Low Forward Voltage : $V_{F(3)} = 0.98V$ (TYP.)

• Fast Reverse Recovery Time : t_{rr}=1.6ns(TYP.)

• Small Total Capacitance : $C_T = 0.5 pF$ (TYP.)

MAXIMUM RATING (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	$ m v_{RM}$	85	V	
Reverse Voltage	$V_{\mathbf{R}}$	80	V	
Maximum (Peak) Forward Current	$I_{\mathbf{FM}}$	200	mA	
Average Forward Current	IO	100	mA	
Surge Current (10ms)	I_{FSM}	1	Α	
Power Dissipation	P	150 ※	mW	
Junction Temperature	T_{j}	125	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C	

Mounted on a glass epoxy circuit board of 20×20mm, pad dimension of 4×4mm.

1-1F1A

PIN ASSIGNMENT

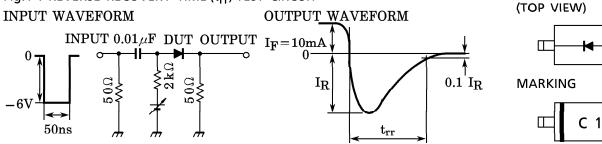
Weight: 1.9mg

TOSHIBA

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _{F (1)}	$I_{\mathbf{F}} = 1 \text{mA}$		0.62		V
	$V_{F(2)}$	$I_{ m F} = 10 { m mA}$	_	0.75	_	
	$v_{F(3)}$	$I_{ m F} = 100 { m mA}$	_	0.98	1.20	
neverse Current	I _{R (1)}	$V_R = 30V$	_	_	0.1	μ A
	I _{R (2)}	$V_R = 80V$	_	_	0.5	
Total Capacitance	C_{T}	$V_R=0$, f=1MHz	_	0.5	3.0	pF
Reverse Recovery Time	t_{rr}	I _F =10mA, Fig.1	_	1.6	4.0	ns

Fig.1: REVERSE RECOVERY TIME (trr) TEST CIRCUIT

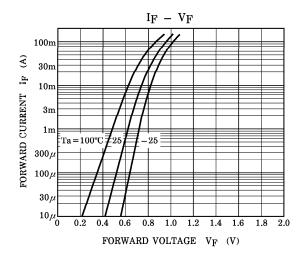


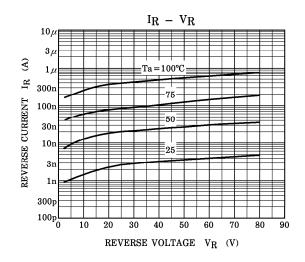
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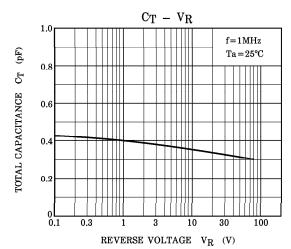
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